Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	656	(438/194,285,574,767).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 07:53
S2	656	(438/194,285,574,767).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/12 17:23
S3	610	S2 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 17:23
S4	656	(438/194,285,574,767).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/13 16:38
S5	610	S4 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:38
S6	67	S5 and (gallium adj nitride or GaN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:07
S7	1	S6 and (atomic adj nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:05
S8	43	S6 and (electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:42

S9	35	S8 and (nitrid$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:55
S10	1	S8 and (nitriding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:55
S11	689	(438/181,182,572,775,777).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 07:54
S16	650	S11 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 08:00
S17	22	S16 and (gallium adj nitride or GaN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 08:20
S18	17	S17 and (electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:10
S19	1	S18 and (atomic near nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 08:03
S20	35905	(gallium adj nitride) or GaN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:11

S21	9287	S20 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:11
S22	220	S21 and (atomic adj nitrogen or nitriding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:12
S23	50	S22 and (atomic adj nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:40
S24	9	S23 and nitriding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:15
S25	7	S24 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:16
S26	199	S22 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 09:41
S27	35905	(gallium adj nitride) or GaN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:01
S28	9287	S27 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:01

S29	220	S28 and (atomic adj nitrogen or nitriding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:01
S30	50	S29 and (atomic adj nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:01
S31	9	S30 and nitriding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:01
S32	656	(438/194,285,574,767).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:09
S33	610	S32 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:09
S34	2	S33 and (surface adj3 stabiliz$5 near method)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:12
S35	24197	(gallium adj nitride) or (GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:31
S36	10865	S35 and (source or gate or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:31
S37	3695	S36 and ((nitride or nitrogen or nitridation or nitr$4) same surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:34

S38	760	S36 and ((nitrogen or nitridation) with surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:34
S39	359	S38 and (transistor or (integrated adj circuit))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:36
S40	343	S39 and (@ad<"20040225" or @rlad<"20040225")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 10:10
S41	50	S35 and ((surface adj treatment) with nitrid$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:39
S42	35960	(gallium adj nitride) or GaN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 15:04
S43	9308	S42 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 15:04
S44	221	S43 and (atomic adj nitrogen or nitriding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 15:04
S45	50	S44 and (atomic adj nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:11
S46	658	(438/194,285,574,767).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 15:33

S47	612	S46 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 15:33
S48	68	S47 and (gallium adj nitride or GaN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 11:32
S49	44	S48 and (electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 15:42
S50	58	S48 and (source or gate or drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 15:43
S51	11	(atomic adj nitrogen) with (produce or generate or create) same (nitrogen near gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:26
S52	11	S51 and (@ad<"20040225" or rlad<"20040225")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:19
S53	88	(atomic adj nitrogen) with (produce or generate or create)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:19
S54	88	S53 and (@ad<"20040225" or rlad<"20040225")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:19

S55	11	atomic adj nitrogen with (produce or generate or create) same (nitrogen near gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:26
S56	658	(438/194,285,574,767).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 11:33
S57	612	S56 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 11:33
S58	6312206	S57 and (aluminum adj nitride or AIN) or (aluminum or Al)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 11:34
S59	45	S57 and (aluminum adj nitride or AIN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 11:56
S60	230	S57 and (aluminum adj nitride or AIN or aluminum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 11:56
S61	184	S60 and (gate or source or drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 13:47
S62	658	(438/194,285,574,767).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 13:48

S63	612	S62 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 13:48
S64	230	S63 and (aluminum adj nitride or AlN or aluminum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 13:48
S65	184	S64 and (gate or source or drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 13:48
S66	45	S65 and (gallium adj nitride or GaN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 14:40
S67	24227	(gallium adj nitride) or (GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 14:41
S68	10883	S67 and (source or gate or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 14:41
S69	762	S68 and ((nitrogen or nitridation) with surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 10:46
S70	361	S69 and (transistor or (integrated adj circuit))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 14:41
S71	345	S70 and (@ad<"20040225" or @rlad<"20040225")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 14:41

S72	11	S71 and (insulation adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 14:41
S73	24281	(gallium adj nitride) or (GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 10:47
S74	10922	S73 and (source or gate or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 10:47
S75	114	S74 and (nitrogen with implantation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 11:11